Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel emitter-collector diode in a TO92 plastic package.

2. Features and benefits

- · High typical DC current gain
- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode

3. Applications

- Compact fluorescent lamps (CFL)
- · Low power electronic lighting ballasts
- · Off-line self-oscillating power supplies (SOPS) for battery charging

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Val	lues		Unit	
Absolute	Absolute maximum rating							
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		7	00		V	
I _c	collector current	DC		1	.5		Α	
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>		2	2.1		W	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
h _{FE}	DC current gain	$I_{C} = 0.5 \text{ A}; V_{CE} = 2 \text{ V}; T_{j} = 25 \text{ °C}$		8	17	25		

NPN power transistor with integrated diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	С	collector]	
3	Е	emitter		B—L
			$\widetilde{\mathbb{Q}}$	I E
			3 2 1 TO-92 (SOT54)	sym131

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
PHD13003C	TO92	PHD13003C,412	Bulk	2000	SOT54	14-Nov-2013
PHD13003C	TO92	PHD13003C,126	Reel	2000	SOT54 wide pitch	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
PHD13003C	D13003C

NPN power transistor with integrated diode

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	700	V
V_{CBO}	collector-base voltage	I _E = 0 A	700	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	400	V
I _c	collector current	DC	1.5	Α
I _{CM}	peak collector current		3	Α
I _B	base current	DC	0.75	Α
I _{BM}	peak base current		1.5	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	2.1	W
T _{stg}	storage temperature		-65 to 150	°C
T _j	junction temperature		150	°C
V _{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	9	V

NPN power transistor with integrated diode

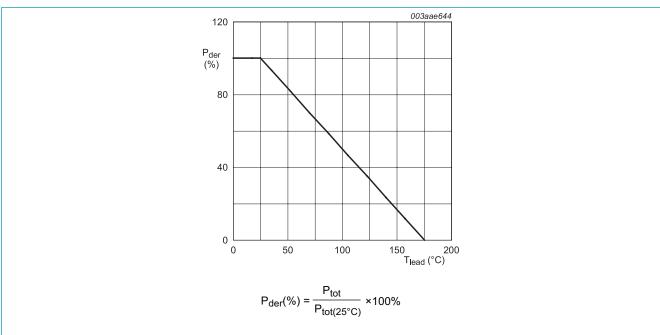


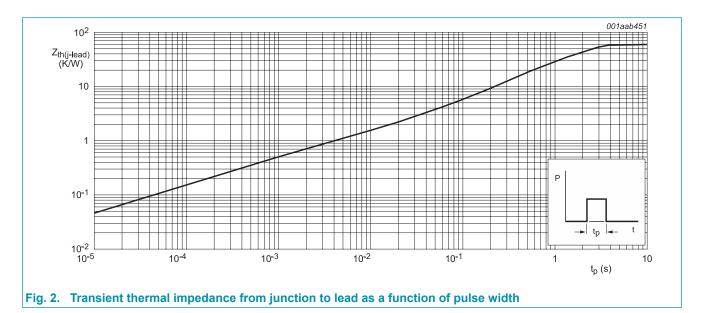
Fig. 1. Normalized total power dissipation as a function of lead temperature

NPN power transistor with integrated diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	Fig. 2	-	-	60	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W



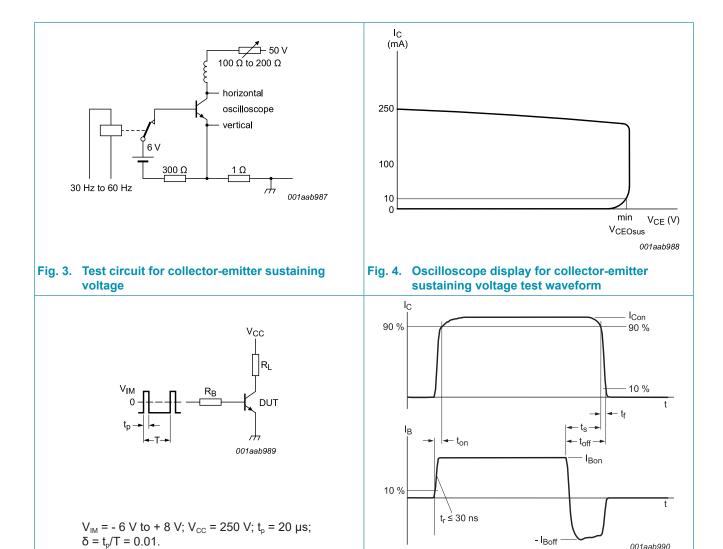
NPN power transistor with integrated diode

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{CES} collector-emitter current	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 700 V	-	-	1	mA
	current	V _{BE} = 0 V; V _{CE} = 700 V; T _j = 100°C	-	-	5	mA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 400 V; I _B = 0 A; T _{lead} = 25°C	-	-	0.1	mA
ЕВО	emitter-base cut-off current	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25^{\circ}\text{C}$	-	-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25^{\circ}\text{C}; \underline{\text{Fig. 3}}; \underline{\text{Fig. 4}}$	400	-	-	V
V _{CEsat}	collector-emitter	$I_{\rm C} = 0.5 \text{A}; I_{\rm B} = 0.1 \text{A}; T_{\rm lead} = 25 ^{\circ} \text{C}$	-	-	0.5	V
	saturation voltage	I _C = 1 A; I _B = 0.25 A; T _{lead} = 25°C	-	-	1	V
		I _C = 1.5 A; I _B = 0.5 A; T _{lead} = 25°C	-	-	1.5	V
V_{BEsat}	base-emitter saturation	I _C = 0.5 A; I _B = 0.1 A; T _{lead} = 25°C	-	-	1	V
	voltage	I _C = 1 A; I _B = 0.25 A; T _{lead} = 25°C	-	-	1.2	V
V _F	forward voltage	I _F = 0.5 A; T _j = 25°C	-	-	1.5	V
h _{FE}	DC current gain	I _C = 0.5 A; V _{CE} = 2 V; T _j = 25°C	8	17	25	
		I _C = 1 A; V _{CE} = 2 V; T _j = 25°C	5	9	15	
Dynamic	characteristics		'	_	_	'
t _{on}	turn-on time	I_{C} = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_{L} = 75 Ω ; T_{lead} = 25 °C; resistive load; <u>Fig. 5</u> ; <u>Fig. 6</u>	-	-	1	μs
t _s	storage time	I_{C} = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_{L} = 75 Ω ; T_{lead} = 25 °C; resistive load; $Fig. 5$; $Fig. 6$	-	-	4	μs
		I_C = 1 A; I_{Bon} = 0.2 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; <u>Fig. 7</u> ; <u>Fig. 8</u>	-	0.8	-	μs
t _f	fall time	I_{C} = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_{L} = 75 Ω ; T_{lead} = 25 °C; resistive load; <u>Fig. 5</u> ; <u>Fig. 6</u>	-	-	0.7	μs
		I_C = 0.5 A; I_{Bon} = 0.1 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.1	-	μs

NPN power transistor with integrated diode



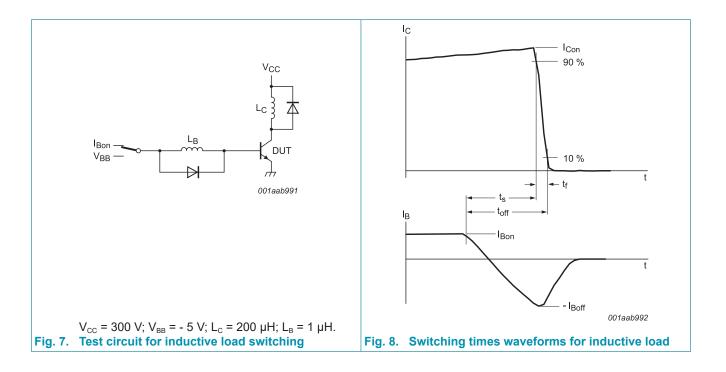
 R_{B} and R_{L} calculated from I_{Con} and I_{Bon} requirements

Fig. 5. Test circuit for resistive load switching

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Fig. 6. Switching times waveforms for resistive load

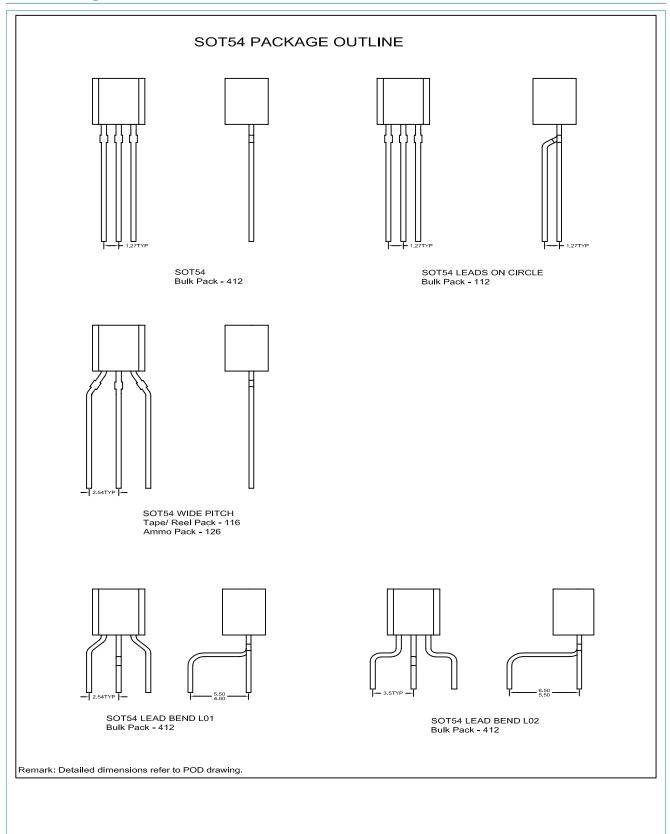
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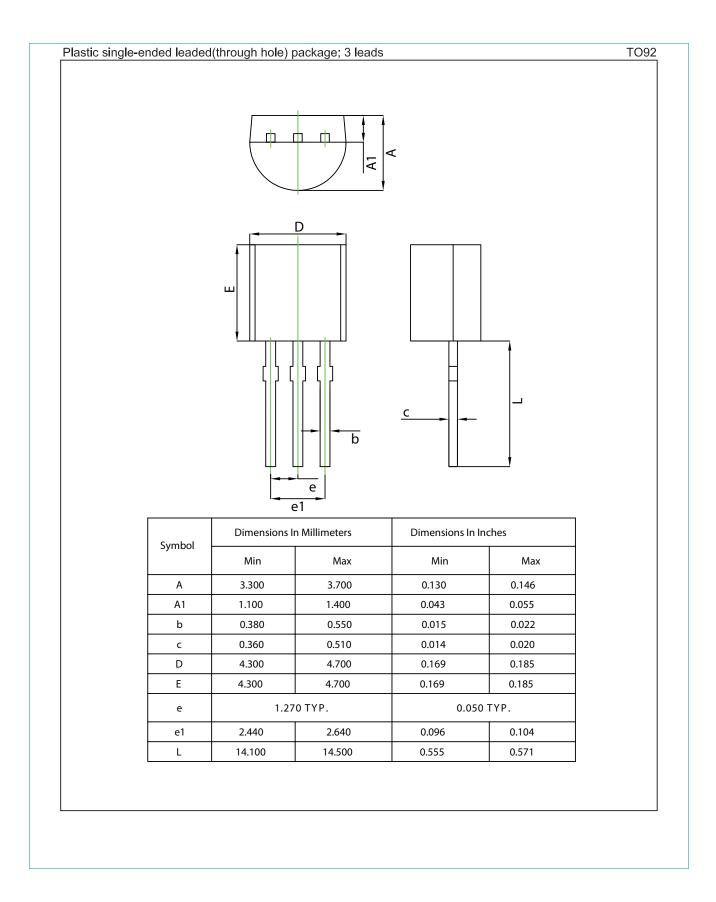
Product data sheet

NPN power transistor with integrated diode

11. Package outline



NPN power transistor with integrated diode



NPN power transistor with integrated diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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NPN power transistor with integrated diode

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Date of release: 10 October 2021

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